## 4. Quick reference data

### Table 1. Quick reference data

i i o i o i o i i o o data					
Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	40	V
drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	-	-	120	Α
total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	395	W
teristics					<u> </u>
drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	0.74	1.06	1.4	mΩ
racteristics					,
gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	13	34	nC
diode					,
recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V	-	39	-	nC
softness factor	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; Fig. 16	-	0.7	-	
	Parameter drain-source voltage drain current total power dissipation teristics drain-source on-state resistance racteristics gate-drain charge  diode recovered charge	drain-source voltage $25  ^{\circ}\text{C} \le T_{j} \le 175  ^{\circ}\text{C}$ drain current $V_{GS} = 10  \text{V};  T_{mb} = 25  ^{\circ}\text{C}$ total power dissipation $T_{mb} = 25  ^{\circ}\text{C};  Fig.  1$ teristics drain-source on-state resistance $V_{GS} = 10  \text{V};  I_{D} = 25  \text{A};  T_{j} = 25  ^{\circ}\text{C};  Fig.  10$ racteristics $ \text{gate-drain charge} \qquad \begin{array}{c} I_{D} = 25  \text{A};  V_{DS} = 32  \text{V};  V_{GS} = 10  \text{V};  Fig.  12;  Fig.  13 \end{array} $ diode $ \begin{array}{c} I_{S} = 25  \text{A};  dI_{S}/dt = -100  \text{A}/\mu\text{s};  V_{GS} = 0  \text{V};  V_{DS} = 20  \text{V};$	$\begin{array}{ c c c } \hline \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} \\ \hline \textbf{drain-source voltage} & 25  ^{\circ}\text{C} \leq T_{j} \leq 175  ^{\circ}\text{C} & - \\ \hline \textbf{drain current} & \textbf{V}_{GS} = 10  \textbf{V};  \textbf{T}_{mb} = 25  ^{\circ}\text{C} & - \\ \hline \textbf{total power dissipation} & \textbf{T}_{mb} = 25  ^{\circ}\text{C};  \textbf{Fig. 1} & - \\ \hline \textbf{teristics} & \\ \hline \textbf{drain-source on-state resistance} & \textbf{V}_{GS} = 10  \textbf{V};  \textbf{I}_{D} = 25  \textbf{A};  \textbf{T}_{j} = 25  ^{\circ}\text{C}; & 0.74 \\ \hline \textbf{resistance} & \textbf{I}_{D} = 25  \textbf{A};  \textbf{V}_{DS} = 32  \textbf{V};  \textbf{V}_{GS} = 10  \textbf{V}; & - \\ \hline \textbf{gate-drain charge} & \textbf{I}_{D} = 25  \textbf{A};  \textbf{V}_{DS} = 32  \textbf{V};  \textbf{V}_{GS} = 10  \textbf{V}; & - \\ \hline \textbf{diode} & \\ \hline \textbf{recovered charge} & \textbf{I}_{S} = 25  \textbf{A};  \textbf{dI}_{S}/\text{dt} = -100  \textbf{A}/\mu\text{s};  \textbf{V}_{GS} = 0  \textbf{V}; & - \\ \hline \textbf{v}_{DS} = 20  \textbf{V} & - \\ \hline \textbf{softness factor} & \textbf{I}_{S} = 25  \textbf{A};  \textbf{dI}_{S}/\text{dt} = -100  \textbf{A}/\mu\text{s};  \textbf{V}_{GS} = 0  \textbf{V}; & - \\ \hline \end{array}$	Parameter         Conditions         Min         Typ           drain-source voltage         25 °C ≤ T <sub>j</sub> ≤ 175 °C         -         -           drain current         V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C         -         -           total power dissipation         T <sub>mb</sub> = 25 °C; Fig. 1         -         -           drain-source on-state resistance         V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Sig. 10         0.74         1.06           racteristics           gate-drain charge         I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Sig. 12; Fig. 13         -         13           diode           recovered charge         I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V         -         39           softness factor         I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; -         -         0.7	Parameter         Conditions         Min         Typ         Max           drain-source voltage         25 °C ≤ T <sub>j</sub> ≤ 175 °C         -         -         40           drain current         V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C         -         -         120           total power dissipation         T <sub>mb</sub> = 25 °C; Fig. 1         -         -         395           teristics           drain-source on-state resistance         V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Pig. 10         0.74         1.06         1.4           racteristics           gate-drain charge         I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Pig. 13         -         13         34           diode           recovered charge         I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; Pig. 20 V         -         39         -           softness factor         I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; Pig. 20 V; Pig

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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G—(F)
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4	
			LFPAK56E; Power- SO8 (SOT1023)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK7J1R4-40H	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch; 4.58 mm x 5.13 mm x 1.03 mm body	SOT1023			

## 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
BUK7J1R4-40H	71H440

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# 8. Limiting values

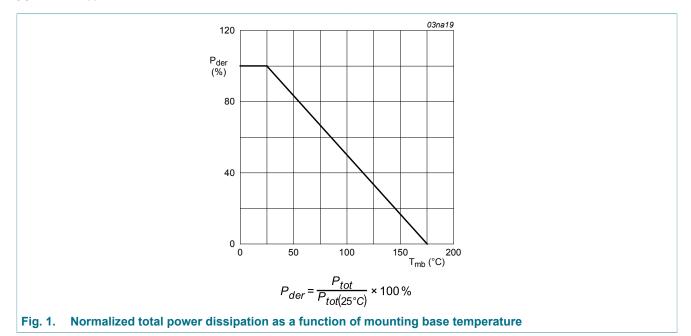
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

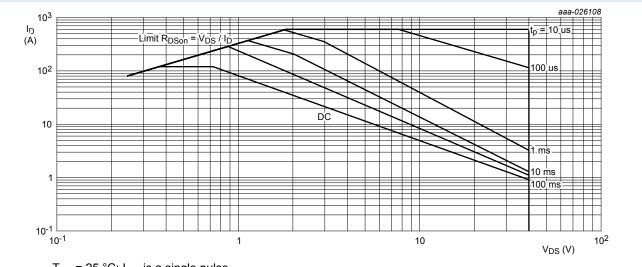
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{GS}$	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	395	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C		-	120	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 2		-	600	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$		-	600	Α
Avalanche r	uggedness			·		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2] [3]	-	253	mJ

<sup>[1] 120</sup>A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

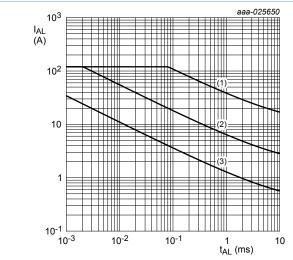


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 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



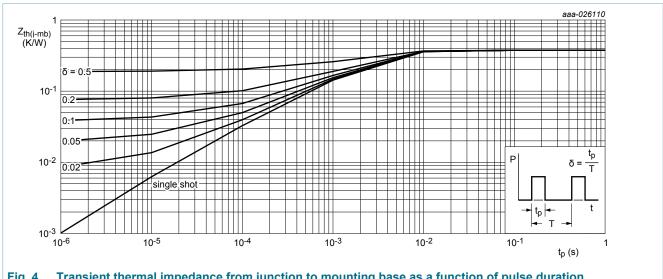
(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.29	0.38	K/W	



Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		1	,		,
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	42	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ} C$	-	39.6	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	38.9	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 8; Fig. 9$	2.4	3	3.6	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = -55 \text{ °C; } Fig. 8$	-	-	4.3	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 175 \text{ °C; } Fig. 8$	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.1	1	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	2.4	10	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	240	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	0.74	1.06	1.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 11	1.05	1.57	2.23	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 11	1.16	1.74	2.45	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11	1.46	2.18	3.05	mΩ
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.4	1	2.5	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	73	126	nC
Q <sub>GS</sub>	gate-source charge	Fig. 12; Fig. 13	-	21	32	nC
Q <sub>GD</sub>	gate-drain charge		-	13	34	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	5436	8155	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	1314	1840	pF
C <sub>rss</sub>	reverse transfer capacitance		-	238	524	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	17	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	43	-	ns
t <sub>f</sub>	fall time	1	-	21	-	ns
Source-drai	in diode		1	1	1	1
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	8.0	1.2	V
		1				

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V	-	37	-	ns
Q <sub>r</sub>	recovered charge		-	39	-	nC
S	softness factor	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; Fig. 16	-	0.7	-	
		$I_S$ = 25 A; $dI_S/dt$ = -500 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; Fig. 16	-	0.56	-	

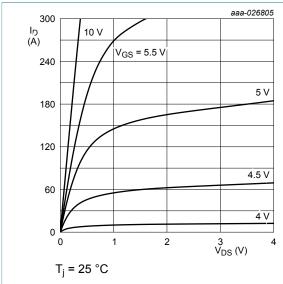


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

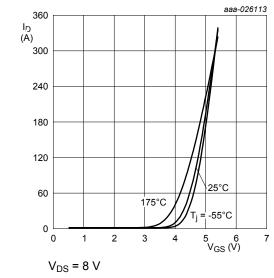


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

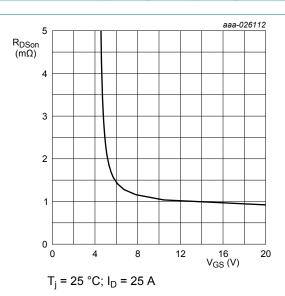
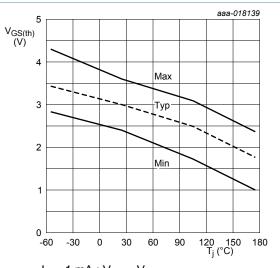


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1 \text{ mA}$ ;  $V_{DS} = V_{GS}$ 

Fig. 8. Gate-source threshold voltage as a function of junction temperature

**Product data sheet** 

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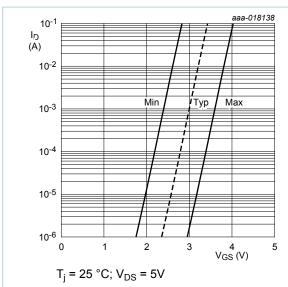


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

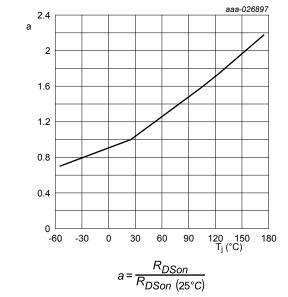


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

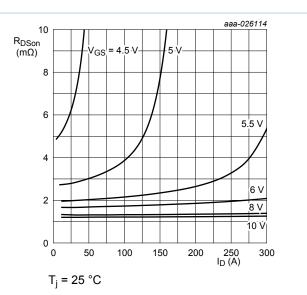


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

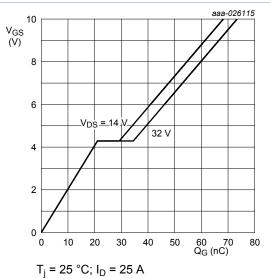


Fig. 12. Gate-source voltage as a function of gate charge; typical values

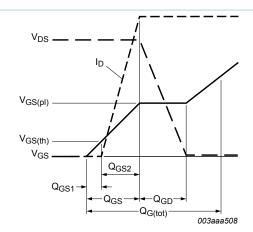
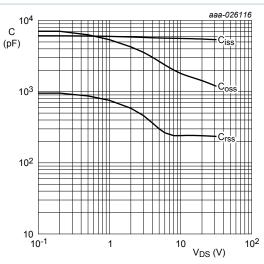


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

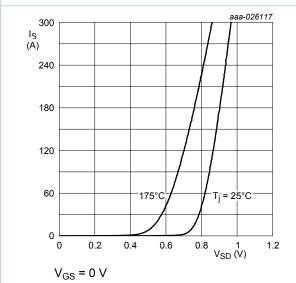
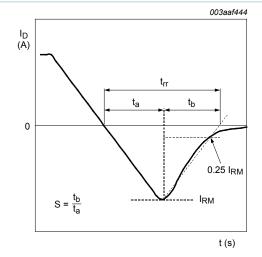


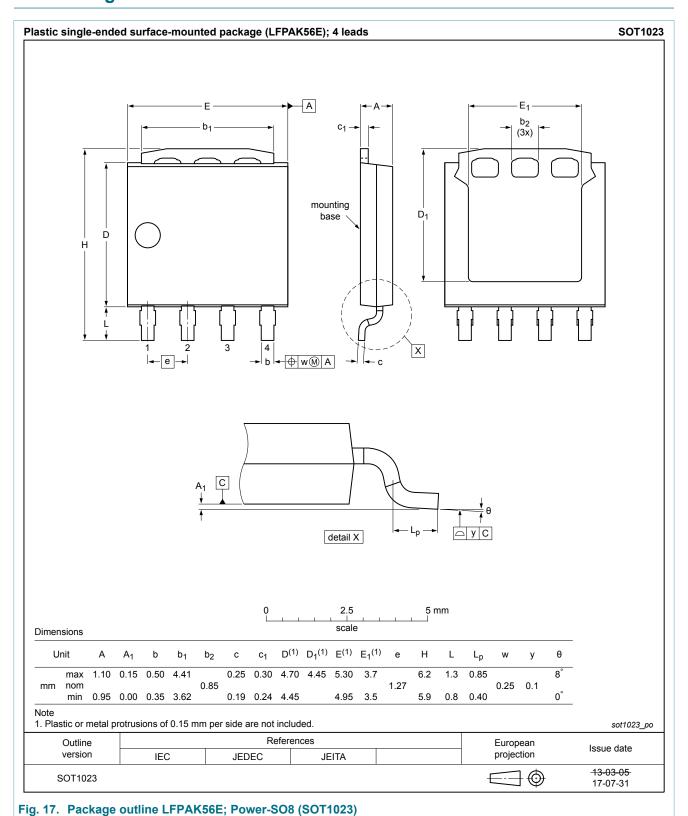
Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $t_{rr} = t_a + t_b$ 

Fig. 16. Reverse recovery waveform definitions

# 11. Package outline



# 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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